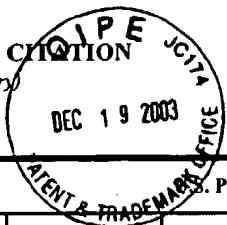


INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

SEC.798

Application Number

09/847,289

Applicant(s)

Kyoung-sub SHIN et al.

Filing Date

May 3, 2001

Group Art Unit

1763

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILED DATE (IF APPROPRIATE)
gag	A	6,136,643	10/24/2000	JENG et al.			
	B	6,150,281 ✓	11/21/2000	KWEAN			
	C	6,344,692 ✓	02/05/2002	IKEMASU et al.			
	D	2001/0034135 A1 ✓	10/25/2001	MIYAKAWA			
gag	E	6,197,670 ✓	03/06/2001	PARK			

FOREIGN PATENT DOCUMENTS

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							YES	NO
gag	F	GB 2 333 179 A ✓	07/14/1999	UK			gag	
gag	G	2000021985 A ✓	01/21/2000	JAPAN			gag	
	H	10041482 A ✓	02/13/1998	JAPAN			gag	
	I	2000040691 A ✓	08/02/2000	JAPAN			gag	
gag	J	2000058482 A ✓	02/25/2000	JAPAN			gag	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

gag	K	Y. Kohyama et al., "A Fully Printable, Self-aligned and Planarized Stacked Capacitor DRAM Cell Technology for 1Gbit DRAM and Beyond", 1997 Symposium on VLSI Technology Digest of Technical Papers, pgs. 17 & 18. ✓

EXAMINER

George Goudreau

DATE CONSIDERED

3-041

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.